

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1.-3.. (canceled).

4. (currently amended): A method ~~according to claim 1,~~ for producing a single crystal from a seed crystal formed of a silicon carbide single crystal by growing the seed crystal, comprising:

disposing the seed crystal in a part of a crucible where crystal growth occurs, with a crystal face of the seed crystal inclined relative to a (0001) plane or (000-1) plane,

wherein the seed crystal is a seed crystal comprising a silicon carbide single crystal cut, polished, then washed and subjected to sacrificial oxidation, and surface-treated by HF washing, and

supplying a vapor gas from silicon carbide as a raw material to the seed crystal formed of a silicon carbide single crystal to grow the seed crystal.

5. (withdrawn): A silicon carbide seed crystal comprising a silicon carbide single crystal cut, polished, then subjected to washing treatment and surface-treated, and having a crystal face inclined relative to a (0001) plane or (000-1) plane.

6. (withdrawn): A silicon carbide seed crystal according to claim 5, wherein the crystal face is inclined by 4 to 45° relative to the (0001) plane or (000-1) plane.

7. (withdrawn): A silicon carbide single crystal that is grown using a silicon carbide seed crystal having a crystal face inclined by 4 to 45° relative to the (0001) plane or (000-1) plane.

8. (currently amended): A method ~~according to claim 2, for producing a single crystal~~
from a seed crystal formed of a silicon carbide single crystal by growing the seed crystal,
comprising:

disposing the seed crystal in a low-temperature region of a crucible where crystal growth
occurs, with a ~~wherein the~~ crystal face of the seed crystal is inclined by 4 to 45° relative to a ~~the~~
(0001) plane or (000-1) plane,

supplying a vapor gas from silicon carbide as a raw material to the seed crystal formed of
a silicon carbide single crystal to grow the seed crystal, and

growing the seed crystal at a crystal growth rate of 0.05 mm/hr or less during an initial
stage of crystal growth and at a crystal growth rate of 1 mm/hr or less thereafter.

9. (currently amended): A method ~~according to claim 2, for producing a single crystal~~
from a seed crystal formed of a silicon carbide single crystal by growing the seed crystal,
comprising:

disposing the seed crystal in a low-temperature region of a crucible where crystal growth
occurs, with a crystal face of the seed crystal inclined relative to a (0001) plane or (000-1) plane,

wherein the seed crystal is a seed crystal comprising a silicon carbide single crystal cut,
polished, then washed and subjected to sacrificial oxidation, and surface-treated by HF washing,

supplying a vapor gas from silicon carbide as a raw material to the seed crystal formed of a silicon carbide single crystal to grow the seed crystal, and
growing the seed crystal at a crystal growth rate of 0.05 mm/hr or less during an initial stage of crystal growth and at a crystal growth rate of 1 mm/hr or less thereafter.

10. (currently amended): A method ~~according to claim 3,~~ for producing a single crystal from a seed crystal formed of a silicon carbide single crystal by growing the seed crystal, comprising:

disposing the seed crystal in a low-temperature region of a crucible where crystal growth occurs, with a crystal face of the seed crystal inclined by 4 to 45° relative to a (0001) plane or (000-1) plane,

wherein the seed crystal is a seed crystal comprising a silicon carbide single crystal cut, polished, then washed and subjected to sacrificial oxidation, and surface-treated by HF washing,

supplying a vapor gas from silicon carbide as a raw material to the seed crystal formed of a silicon carbide single crystal to grow the seed crystal, and
growing the seed crystal at a crystal growth rate of 0.05 mm/hr or less during an initial stage of crystal growth and at a crystal growth rate of 1 mm/hr or less thereafter.

11. (previously presented): A method according to claim 8, wherein the seed crystal is a seed crystal comprising a silicon carbide single crystal cut, polished, then washed and subjected to sacrificial oxidation, and surface-treated by HF washing.